

1. General description

Planar passivated high commutation three quadrant triac in a TO220F "full pack" plastic package. This triac is intended for use in motor control circuits where very high blocking voltage can occur. It is used in applications where "high junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Over-voltage withstand capability to IEC 61000-4-5
- Planar passivated for voltage ruggedness and reliability
- High immunity to false turn on by dV/dt
- Triggering in three quadrants only
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant
- Package meets UL1557 isolation test requirement rated at 2500V RMS

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls e.g. vertical axis washing machines

4. Quick reference data

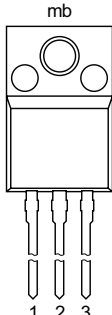
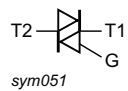
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	1000	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_n \leq 136\text{ °C}$; Fig.1 ; Fig. 2 ; Fig. 3	-	-	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	25	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	27.5	A
T_j	junction temperature		-	-	150	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	35	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	35	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	-	40	mA
V_T	on-state voltage	$I_T = 3\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	-	1.5	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$; $T_j = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA202X-1000CT	TO220F	BTA202X-1000CTQ	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA202X-1000CT	BTA202X 1000CT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 136\text{ °C}$; Fig.1 ; Fig. 2 ; Fig. 3	-	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	25	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	27.5	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine wave pulse	-	3.125	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	$A/\mu s$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}C$
T_j	junction temperature		-	150	$^{\circ}C$

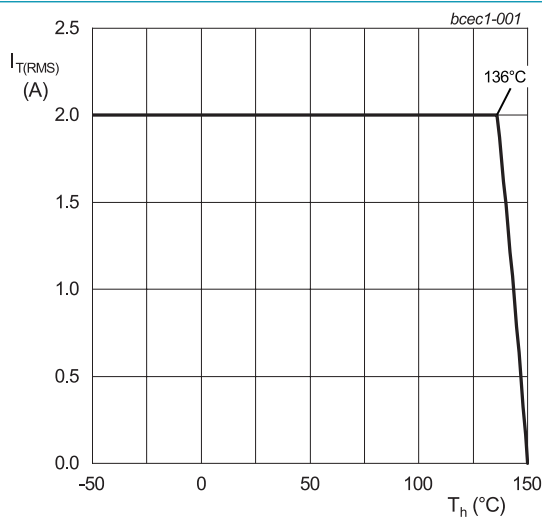


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

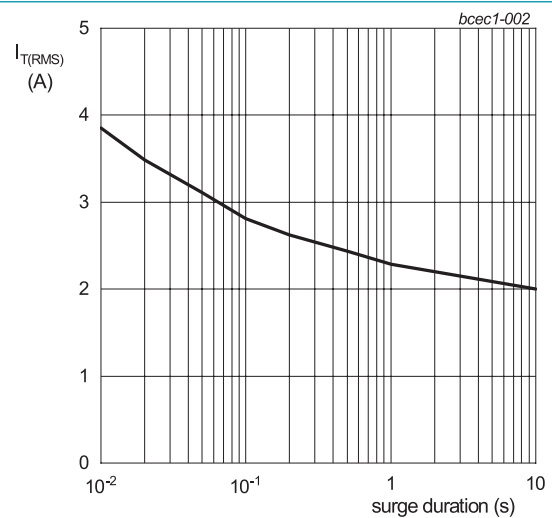


Fig. 2. RMS on-state current as a function of surge duration; maximum values
 $f = 50\text{ Hz}$; $T_h = 136\text{ °C}$

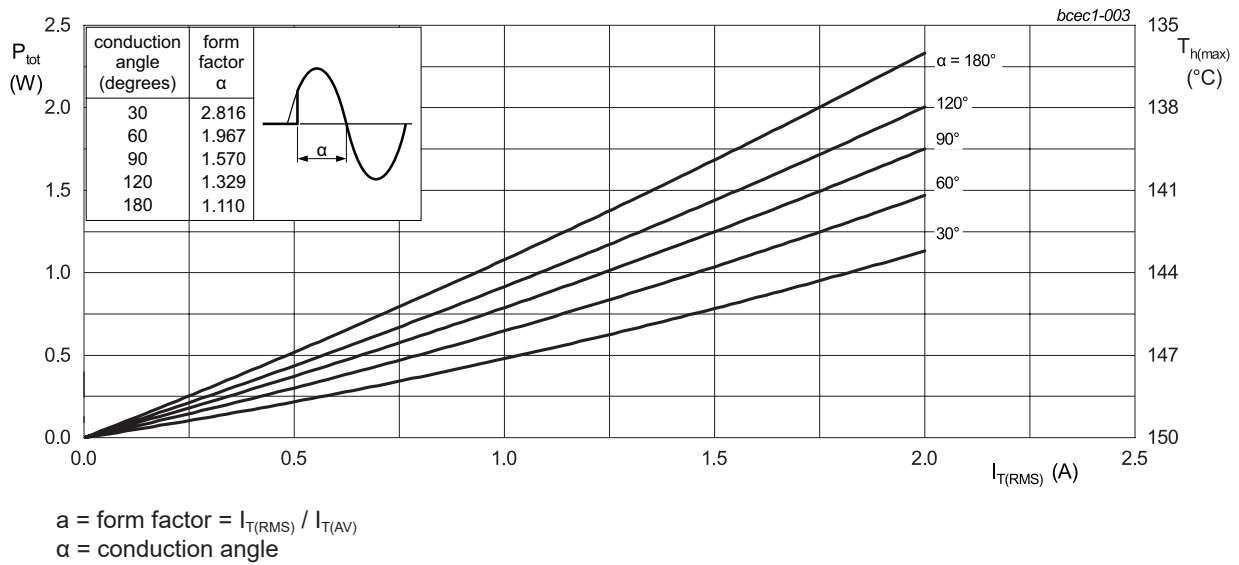


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

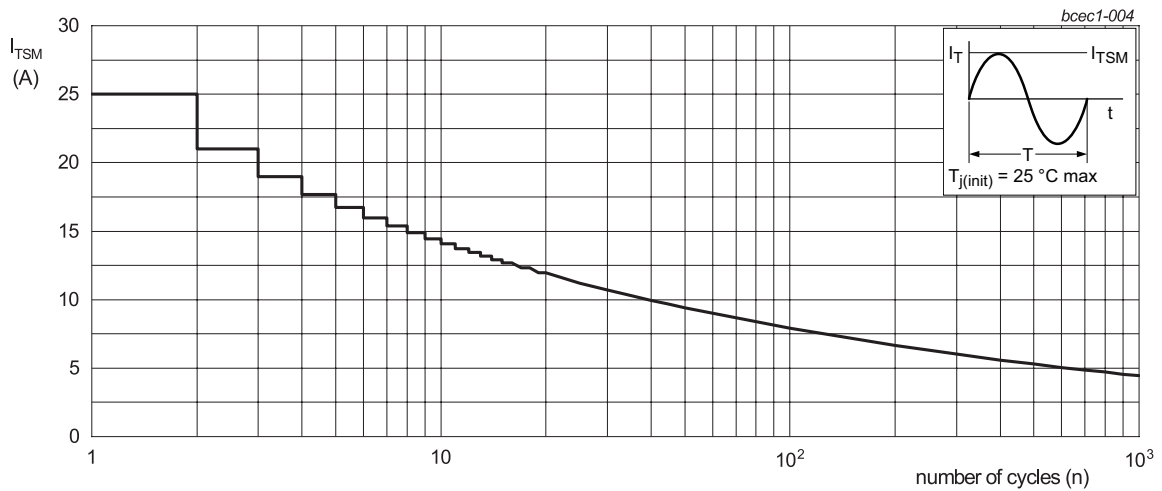


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

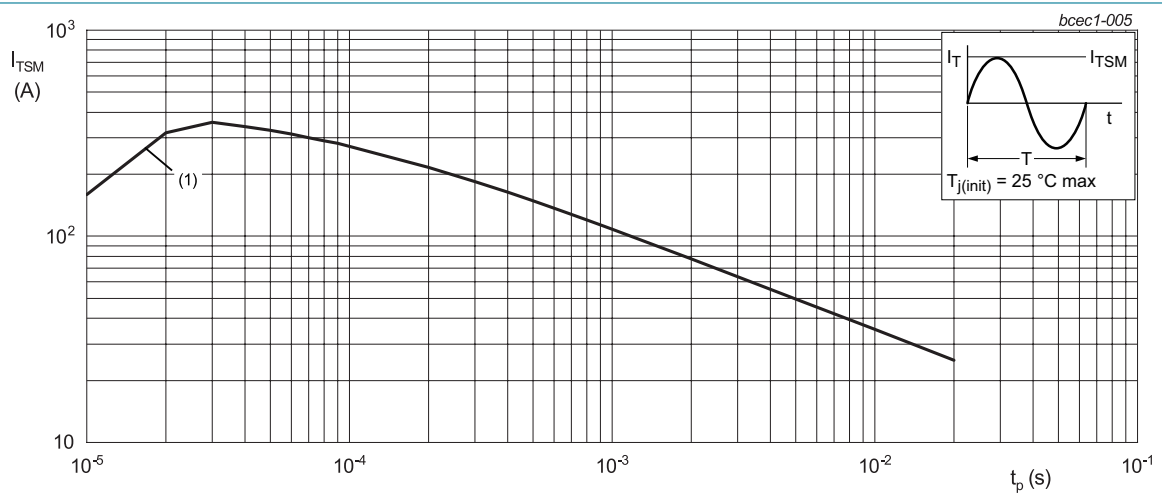


Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; with heatsink compound; Fig. 6	-	-	6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

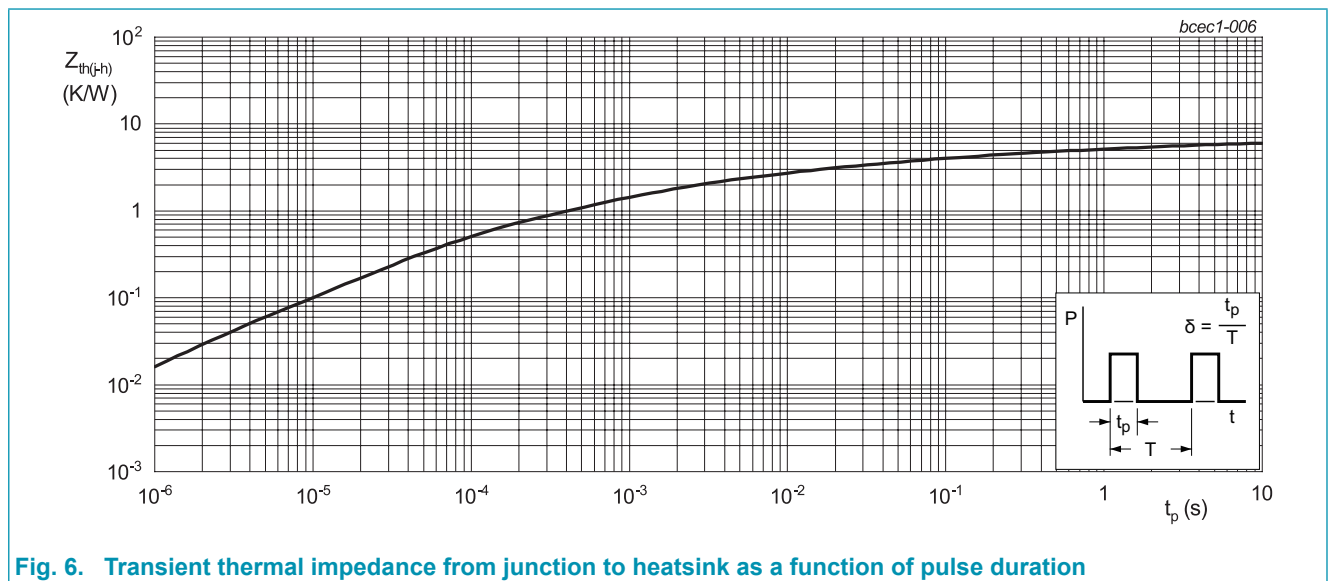


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

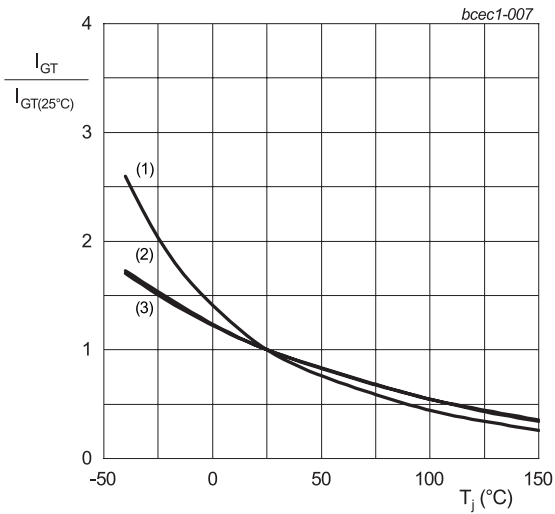
Table 7. Isolation Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_{mb} = 25\text{ }^\circ\text{C}$	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$; $T_{mb} = 25\text{ }^\circ\text{C}$	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 7	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 7	-	-	35	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 8	-	-	60	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	70	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 8	-	-	60	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9	-	-	40	mA
V_T	on-state voltage	$I_T = 3\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10	-	-	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$ Fig. 11	-	0.8	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ °C}$	0.2	0.45	-	V
I_D	off-state current	$V_D = 1000\text{ V}$; $T_J = 25\text{ °C}$	-	-	10	μA
		$V_D = 1000\text{ V}$; $T_J = 150\text{ °C}$	-	-	1	mA
I_R	reverse current	$V_R = 1000\text{ V}$; $T_J = 25\text{ °C}$	-	-	10	μA
		$V_R = 1000\text{ V}$; $T_J = 150\text{ °C}$	-	-	1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit; snubberless condition	6	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	8	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	10	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

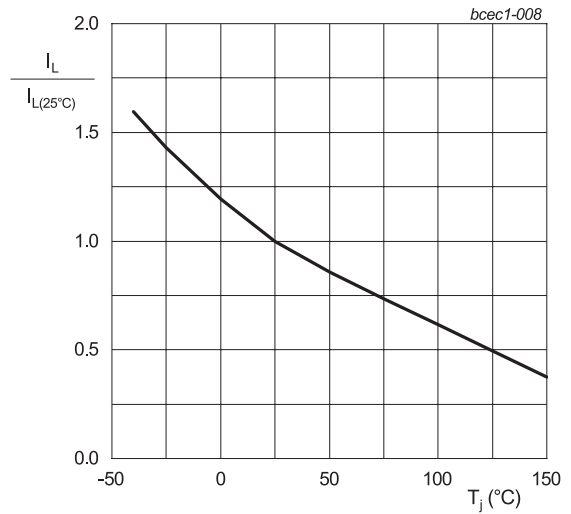


Fig. 8. Normalized latching current as a function of junction temperature

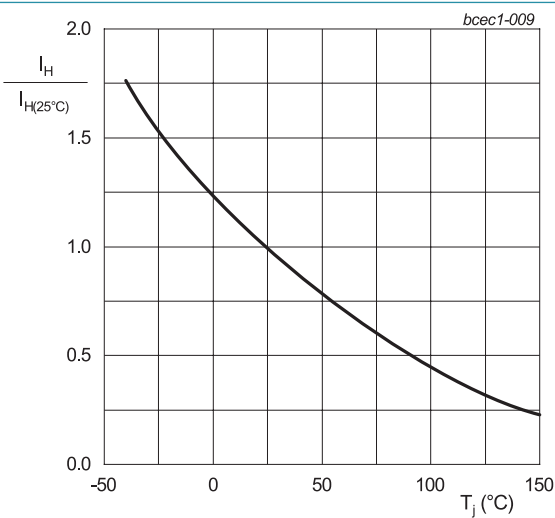
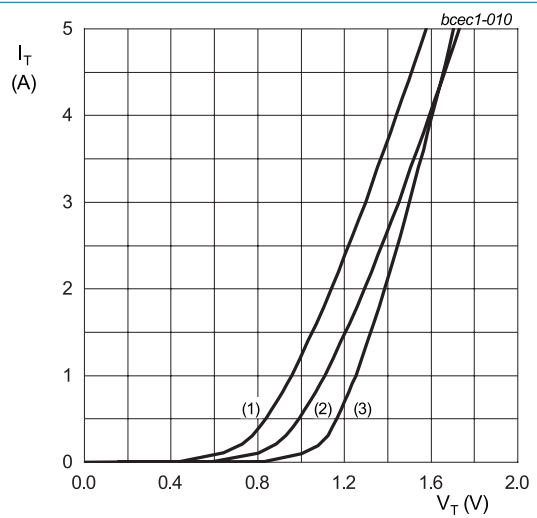


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.101\text{ V}; R_s = 0.0875\ \Omega$
- (1) $T_j = 150^\circ\text{C}$; typical values
 - (2) $T_j = 150^\circ\text{C}$; maximum values
 - (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

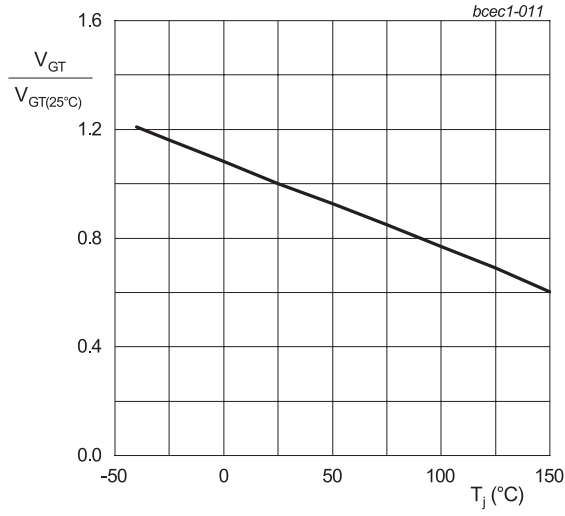
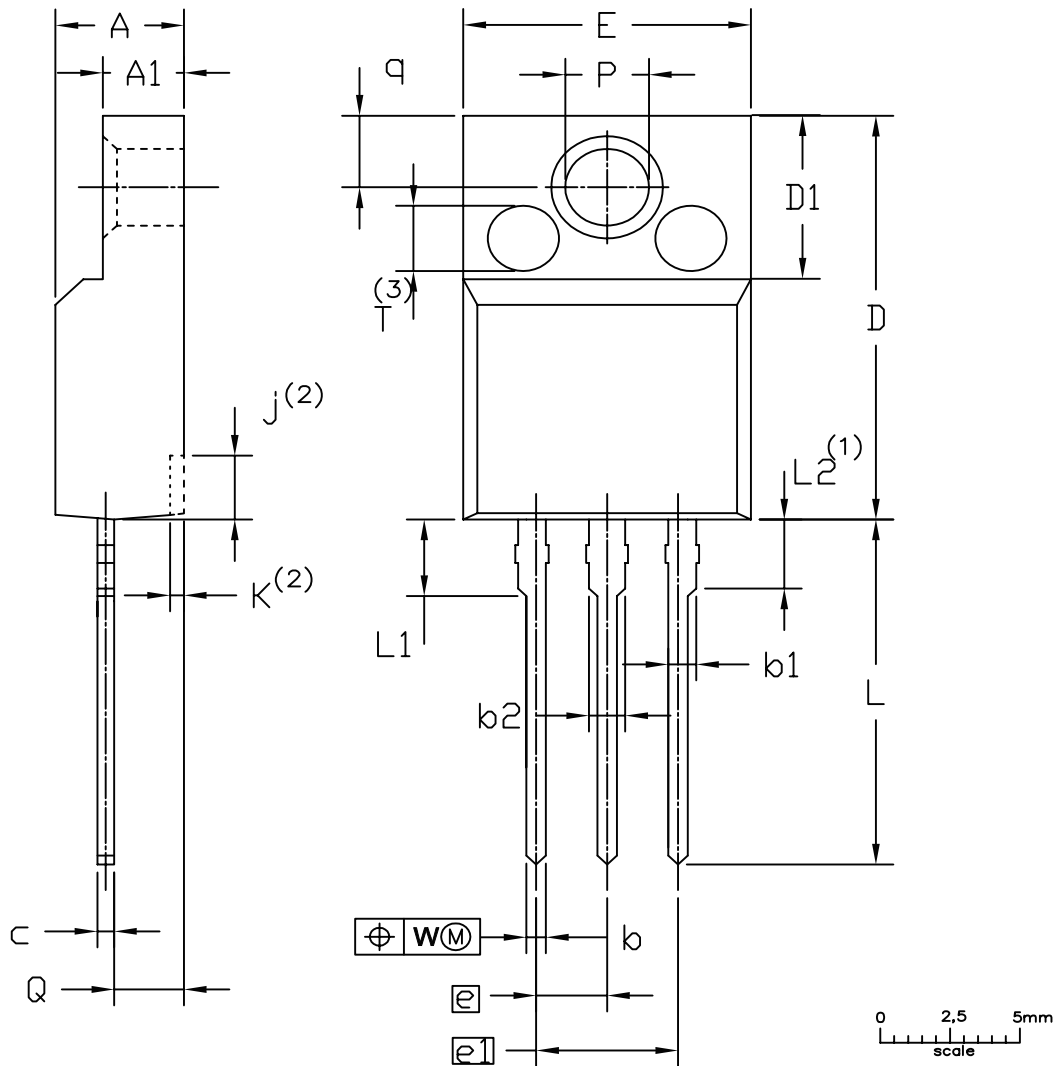


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁	E	e	e ₁	j ⁽²⁾	K ⁽²⁾	L	L ₁	L ₂ ⁽¹⁾ max.	P	Q	q	W	T ⁽³⁾
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7			1.7	0.4	13.5	2.79		3.0	2.3	2.6		

Notes

1. Terminal dimensions within this zone are uncontrolled
2. Dot lines area designs may vary
3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3 LEADS TO220F			2013-11-14

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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